

MJE13003FT (3DD13003FT)

硅 NPN 半导体三极管/SILICON NPN TRANSISTOR

用途:主要用于节能灯、日光灯电子镇流器及其它开关、振荡电路。

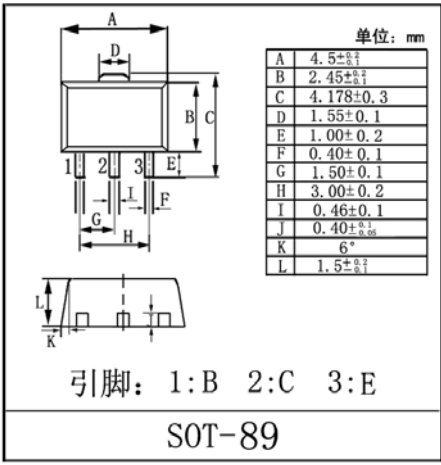
Purpose: High frequency electronic lighting ballast applications, converters, inverters, switching regulators, etc.

极限参数/Absolute maximum ratings(Ta=25℃)

参数符号 Symbol	数值 Rating	单位 Unit
V _{CB0}	600	V
V _{CE0}	400	V
V _{EB0}	9.0	V
I _C	0.5	A
P _C	500	mW
*P _C	1.0	W
T _j	150	℃
T _{stg}	-55~150	℃

*mounted on ceramic substrate(250mm²×0.8t)

*贴装于 250mm²×0.8t 的陶瓷板上。



电性能参数/Electrical characteristics(Ta=25℃)

参 数 符 号 Symbol	测试条件 Test condition	数值 Rating			单位 Unit
		最小值 Min	典型值 Typ	最大值 Max	
V _{CB0}	I _C =1mA I _E =0	600			V
V _{CE0}	I _C =10mA I _B =0	400			V
V _{EB0}	I _E =1mA I _C =0	9.0			V
I _{CB0}	V _{CB} =600V I _E =0			0.1	mA
I _{CE0}	V _{CE} =400V I _B =0			0.1	mA
I _{EB0}	V _{EB} =9.0V I _C =0			0.1	mA
h _{FE}	V _{CE} =5.0V I _C =200mA	10		40	
V _{CE(sat)}	I _C =200mA I _B =40mA			0.5	V
V _{BE(sat)}	I _C =200mA I _B =40mA			1.2	V
f _T	V _{CE} =10V I _C =50mA f=1.0MHz	5.0			MHz
t _f	V _{CE} =5V I _C =100mA (UI9600)			0.6	μs
t _S				4.0	μs

印章/Marking: H03F

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